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PATENT Atty. Dkt. AMAT/5351/CPI/L/B/PJS

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Mak, et al.

Serial No.: 09/885,609

Confirmation No.: 5337

Filed:

June 20, 2001

For:

System and Method to Form a Composite Film Stack Utilizing Sequential Deposition Techniques

Group Art Unit: 2818

Examiner:

R. Berry

CERTIFICATE OF MAILING 37 CFR 1.8

I hereby certify that this correspondence is being deposited on May 2, 2003 with the United States Postal Service as First Class Mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22318-1450.

18-21-12

Signature

MAIL STOP DD Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Supplemental Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Supplemental Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/APPM/5351/BTP.

Respectfully submitted,

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U.S. Department of Commerce, Patent and Trademark Office						Docket No.		Serial No.		
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT						Applicant		Confirmation	No.:	
			Mak, et al.		5337					
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J.S. Patent I				(A)	TRADEMIRE					
Examiner	Jocail	Document Number	Issu	ıe	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate		
-	A1	6,548,424	04/	15/03	Putkonen	438	785	04/16/01		
SPE 3	A 2	6,534,395		18/03	Werkhoven, et al.	438	627	03/06/01		
<u> </u>	3	6,511,539		28/03	Raaijmakers, et al.	. 117	102	09/08/99 05/31/01		
ANY L' LOST	\$\frac{3}{6}\text{A4}			22/02	Lee, et al.		763			
TA TRADEMAN	A5	6,458,701	10/01/02		Chae, et al.	438	680	10/12/00		
4 IAAC	A6	6,416,577		/09/02	Suntoloa, et al.	117 88		06/07/00		
	A7	6,399,491	06/04/02		Jeon, et al.	438	680	04/06/01		
	A8	6,372,598	04/16/02		Kang, et al.	438	399	06/16/99		
	A9	6,348,376	02/19/02		Lim, et al.	438	253	01/19/01		
	A10	6,342,277	01/29/02		Sherman	427	562	04/14/99		
	A11	6,333,260	12/25/01		Kwon, et al.	438	643	06/24/99		
	A12	6,287,965	09/11/01		Kang, et al.	438	648	02/23/00		
	A13	6,207,487	_	/27/01	Kim, et al.	438	238	10/12/99		
	A14	6,197,683	03/06/01		Kang, et al.	438	643	09/18/98		
Foreign Pa	L									
*Examiner Initial		Document		Date	Country	Class	Subclass	Transla	tion	
		Number						YES	NC	
	B1	02/45167		06/06/02	WO	H01L	27/00			
	B2	02/067319		08/29/02	WO	H01L	21/768		+ =	
	В3	00/79576		12/28/00	WO	H01L	21/205			
OTHER AR	 ≀T	1								
*Examiner Initial		Ì			rtinent Pages, Etc.					
	C1	Diffusion Barr	riers,'	' J. Vacuun	hanced Atomic Layen Sci. & Tech. B., Vo	ol. 18, No. 4	+ (July 2000)), pp. 2010-20		
	C2	Ritala, et al. " Atomic Layer	Atom	nic Force M axy," Thin S	icroscopy Study of Solid Films, Vol. 228	Titanium Di 3, No. 1-2 (1	oxide Thin F 5 May 1993	ilms Grown b), pp.32-35	y 	
Examiner			· ·			Date Co				

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INFORMATION	/				Docke			Sheet 2 of 3
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U.S. Patent Docu	uments	17	TRADENIE!					Group
Initial	Document		THAUL		June 20,	2001	_ 2	2818
ALPS A1	Da	sue ate	Applicant(s)		<u> </u>			
10.5	6,042,652 03	/28/00	ivame		Class	Subcla	ass Fi	ling Date If
MAY 2 2 2003 PA3	5,526,244	/11/96	Hyun, et al.		117	+	Ap	opropriate
MAI 2 2 2003 14A3		01/03	Bishop	-	362	719		/07/99
A4 A5	2003/0070		Todd, et al.	-		147	05,	/24/93
A5	2003/00400	17/03	Shero, et al.		27	255.27	1	11/02
A6 2	2003/0000	3/03	Haukka, et al.		28	704		26/02
A7 2	2003/000		Werkhoven, et a	43		778		22/02
A8 20	003/00405		Elers, et al.	-		640	09/2	
A9 20	102/040=		Kim, et al.	42	7	569	09/17	
A10 20	002/018/631 12/12/	/02	Kim, et al.	438	3	778		
A11 200	002/0187256 12/12/	02	Elers, et al.	438	6	37	05/31	
200	02/0182320 12/05/0			427	9		12/05/	
200	02/0177282 11/28/0	,,	Leskela, et al.	427	25	70	07/30/	
200	2/0135071 09/26/01		Song	438	30	-	03/15/0	1
Oreign Patent P			(ang, et al.	257	-		12/18/0	i i
oreign Patent Docume		- M	larsh	257	76		01/16/0	2
itial Docur	ment Date				75 ·	C	04/30/02	2
5	_	Co	Duntry	Class				
B1 00/158		00		01435	Sub	class	Trans	lation
B2 99/299	924 03/23/0	,)	C23C			YES	NO
B3 90/045	100/17/9	, ,,,)		16/0			
IER ART	01/14/9	1/14/99 WO		C23C	10/04			+
miner Including	9 Author Till	_		C30B	25/14		<u> </u>	
C1 Ritale	g Author, Title, Date, Pe	ertinent P	ages, Etc					
Ritala, e	et al. "Growth of Titani ol. 225, No. 1-2 (25 M l. "Chemical Vapor De Soc. Symp Press	ilim C:	. –10,					
C2 Min. of	JI. 225, No. 1-2 (25 N	larch 10	(ide Thin Films by	Atomic				
Mat. Rec	J. "Chemical Vapor De Soc. Symp. Proc. Vo	enneitie-	95) pp. 288-95		Layer Ep	oitaxy," T	hin Soli	d
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant. T:\CLIENTS\APPM\5000-5999\5351\PTO\PTO_1449_051703.DOC

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U.S. Department of Commerce, Patent and Trademark Office) .	Serial No.		
(PTO Form 1449 modified)						51/CPI/L/B/	09/885,609		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT							Confirmation No.:		
			Mak, et al.		5337				
(Use severa	al sheet	s if necessary)	Filing Date	•	Group				
	E	Examiner R. B	June 20, 2001		2818				
U.S. Patent	Docur	ments	ENT & TE	ADEMA					
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate		
	A1	2002/0109168	08/15/02	Kim, et al.	257	295	01/30/02		
PE	A2	2002/0106536	08/08/02	Lee, et al.	428	702	02/02/01		
1 2 2003 ET	А3	2002/0105088	08/08/02	Yang, et al.	257	774	10/31/01		
	A4	2002/0081844	06/27/02	Jeon, et al.	438	680	02/28/02		
& TRADEMARK	A5	2002/0076837	06/20/02	Hujanen, et al.	438	3	11/28/01		
	A6	2002/0076507	06/20/02	Chiang, et al.	427	569	10/24/01		
	A7	2002/0074588	06/20/02	Lee	257	306	07/06/01		
	A8	2002/0061612	05/23/02	Sandhu, et al.	438	151	01/14/02		
	A9	2002/0048635	04/25/02	Kim, et al.	427	331	08/08/99		
	A10	2002/0021544	02/21/02	Cho, et al.	361	200	08/07/01		
	A11	2002/0000598	01/03/02	Kang, et al.	257	301	07/26/01		
	A12	2001/0054730	12/27/01	Kim, et al.	257	301	05/23/01 06/05/01 02/22/01		
	A13	2001/0050039	12/13/01	Park	117	102			
	A14	2001/0028924	09/27/01	Raaijmakers, et al.	. 365	200			
Foreign Pa	tent D	ocuments							
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translat YES	ion NO	
	B1	98/51838	11/19/98	wo	C23C	16/06			
	B2	2001-111000	12/26/00	JP	H01L	29/00			
	B3	2,355,747	05/02/01	GB	C23C	16/44			
OTHER AF	.l	_,							
*Examiner Initial		Including Author	Title, Date, Per	tinent Pages, Etc.		02.	4 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0		
	C1	Klaus, et al. "Atomically Controlled Growth of Tungsten and Tungsten Nitride Using Sequential Surface Reactions," Applied Surface Science, 162-163 (2000) 479-491							
	C2								
Examiner					Date Con	sidered			